21. The composition of claim 20, wherein the at least one carboxylic acid comprises citric acid, maleic acid, fumaric acid, lactic acid, glycolic acid, oxalic acid, tartaric acid, succinic acid, or benzoic acid.

22. The composition of claim 21, wherein the at least one carboxylic acid comprises citric acid.

23. The composition of claim 1, wherein the composition comprises the at least one carboxylic acid in an amount from about 0.1 wt% to about 1.5 wt%.

24. The composition of claim 1, wherein the at least one Group II metal cation comprises Mg^{2+}, Ca^{2+}, Sr^{2+}, or Ba^{2+}.

25. The composition of claim 1, wherein the at least one Group II metal cation comprises Ca^{2+}.

26. The composition of claim 1, wherein the composition comprises the at least one Group II metal cation in an amount from about 5 ppm to about 40 ppm.

27. The composition of claim 1, wherein the composition has a pH of at least about 13.

28. A method, comprising:

contacting a semiconductor substrate containing a photoresist or a photoresist residue with the composition of claim 1 to remove the photoresist or photoresist residue.

29. The method of claim 28, further comprising rinsing the semiconductor substrate with a rinse solvent after the contacting step.